

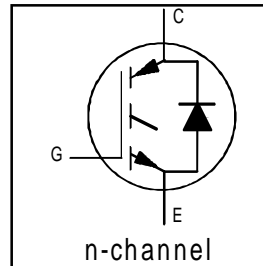
IRG4BC20KD

INSULATED GATE BIPOLAR TRANSISTOR WITH
ULTRAFAST SOFT RECOVERY DIODE

Short Circuit Rated
UltraFast IGBT

Features

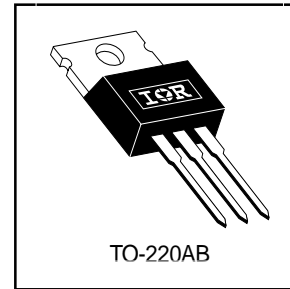
- Short Circuit Rated UltraFast: Optimized for high operating frequencies >5.0 kHz , and Short Circuit Rated to 10 μ s @ 125°C, $V_{GE} = 15V$
- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency than previous generation
- IGBT co-packaged with HEXFRED™ ultrafast, ultra-soft-recovery anti-parallel diodes for use in bridge configurations
- Industry standard TO-220AB package



$V_{CES} = 600V$
$V_{CE(on) typ.} = 2.27V$
@ $V_{GE} = 15V, I_C = 9.0A$

Benefits

- Latest generation 4 IGBTs offer highest power density motor controls possible
- HEXFRED™ diodes optimized for performance with IGBTs. Minimized recovery characteristics reduce noise, EMI and switching losses
- This part replaces the IRGBC20KD2 and IRGBC20MD2 products
- For hints see design tip 97003



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	16	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	9.0	
I_{CM}	Pulsed Collector Current ①	32	
I_{LM}	Clamped Inductive Load Current ②	32	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	7.0	
I_{FM}	Diode Maximum Forward Current	32	
t_{sc}	Short Circuit Withstand Time	10	μ s
V_{GE}	Gate-to-Emitter Voltage	± 20	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	60	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	24	
T_J	Operating Junction and Storage Temperature Range	-55 to +150	$^\circ C$
T_{STG}			
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	—	—	2.1	$^\circ C/W$
$R_{\theta JC}$	Junction-to-Case - Diode	—	—	3.5	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	—	80	
Wt	Weight	—	2 (0.07)	—	g (oz)

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Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)CES}	Collector-to-Emitter Breakdown Voltage ^③	600	—	—	V	V _{GE} = 0V, I _C = 250μA
ΔV _{(BR)CES} /ΔT _J	Temperature Coeff. of Breakdown Voltage	—	0.49	—	V/°C	V _{GE} = 0V, I _C = 1.0mA
V _{CE(on)}	Collector-to-Emitter Saturation Voltage	—	2.27	2.8	V	I _C = 9.0A I _C = 16A I _C = 9.0A, T _J = 150°C
		—	3.01	—		
		—	2.43	—		
V _{GE(th)}	Gate Threshold Voltage	3.0	—	6.0		V _{CE} = V _{GE} , I _C = 250μA
ΔV _{GE(th)} /ΔT _J	Temperature Coeff. of Threshold Voltage	—	-10	—	mV/°C	V _{CE} = V _{GE} , I _C = 250μA
g _{fe}	Forward Transconductance ^④	2.9	4.3	—	S	V _{CE} = 100V, I _C = 9.0A
I _{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	V _{GE} = 0V, V _{CE} = 600V V _{GE} = 0V, V _{CE} = 600V, T _J = 150°C
		—	—	1000		
V _{FM}	Diode Forward Voltage Drop	—	1.4	1.7	V	I _C = 8.0A I _C = 8.0A, T _J = 150°C
		—	1.3	1.6		
I _{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V _{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q _g	Total Gate Charge (turn-on)	—	34	51	nC	I _C = 9.0A V _{CC} = 400V V _{GE} = 15V See Fig.8
Q _{ge}	Gate - Emitter Charge (turn-on)	—	4.9	7.4		
Q _{gc}	Gate - Collector Charge (turn-on)	—	14	21		
t _{d(on)}	Turn-On Delay Time	—	54	—	ns	T _J = 25°C I _C = 9.0A, V _{CC} = 480V V _{GE} = 15V, R _G = 50Ω
t _r	Rise Time	—	34	—		
t _{d(off)}	Turn-Off Delay Time	—	180	270		
t _f	Fall Time	—	72	110		
E _{on}	Turn-On Switching Loss	—	0.34	—	mJ	Energy losses include "tail" and diode reverse recovery See Fig. 9,10,14
E _{off}	Turn-Off Switching Loss	—	0.30	—		
E _{ts}	Total Switching Loss	—	0.64	0.96		
t _{sc}	Short Circuit Withstand Time	10	—	—	μs	V _{CC} = 360V, T _J = 125°C V _{GE} = 15V, R _G = 50Ω, V _{CPK} < 500V
t _{d(on)}	Turn-On Delay Time	—	51	—	ns	T _J = 150°C, See Fig. 11,14 I _C = 9.0A, V _{CC} = 480V V _{GE} = 15V, R _G = 50Ω
t _r	Rise Time	—	37	—		
t _{d(off)}	Turn-Off Delay Time	—	220	—		
t _f	Fall Time	—	160	—		
E _{ts}	Total Switching Loss	—	0.85	—	mJ	Energy losses include "tail" and diode reverse recovery
L _E	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
C _{ies}	Input Capacitance	—	450	—	pF	V _{GE} = 0V V _{CC} = 30V f = 1.0MHz See Fig. 7
C _{oes}	Output Capacitance	—	61	—		
C _{res}	Reverse Transfer Capacitance	—	14	—		
t _{rr}	Diode Reverse Recovery Time	—	37	55	ns	T _J = 25°C See Fig. 14 T _J = 125°C
		—	55	90		
I _{rr}	Diode Peak Reverse Recovery Current	—	3.5	5.0	A	T _J = 25°C See Fig. 15 T _J = 125°C
		—	4.5	8.0		
Q _{rr}	Diode Reverse Recovery Charge	—	65	138	nC	T _J = 25°C See Fig. 16 T _J = 125°C
		—	124	360		
di _(rec) M/dt	Diode Peak Rate of Fall of Recovery During t _b	—	240	—	A/μs	T _J = 25°C See Fig. 17 T _J = 125°C
		—	210	—		

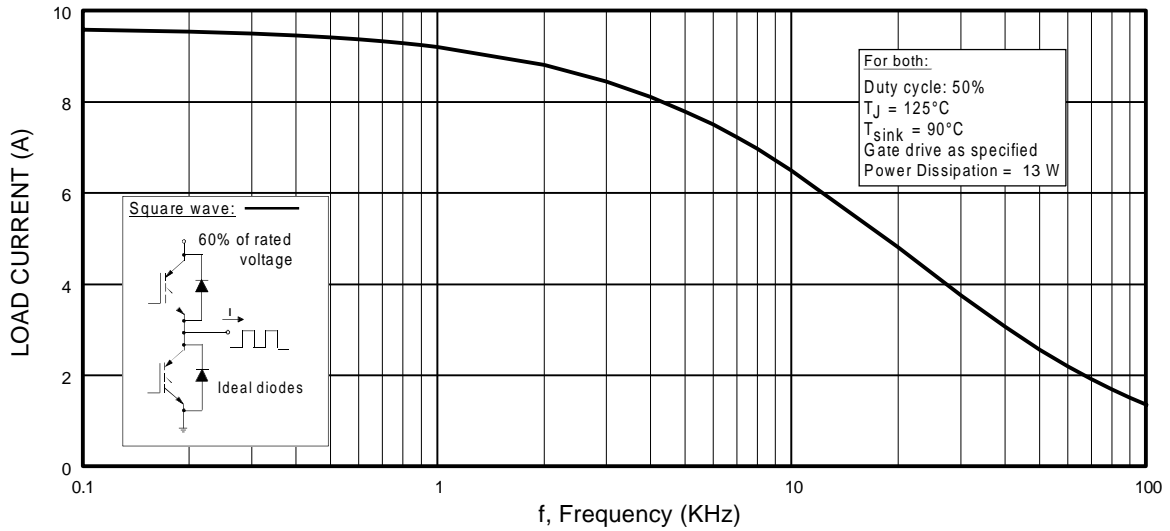


Fig. 1 - Typical Load Current vs. Frequency
 (Load Current = I_{RMS} of fundamental)

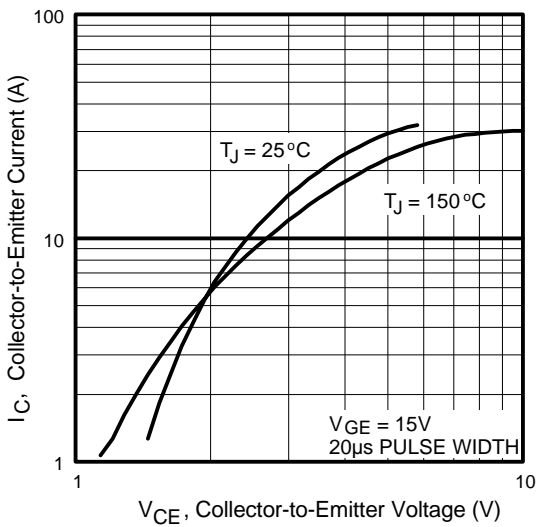


Fig. 2 - Typical Output Characteristics

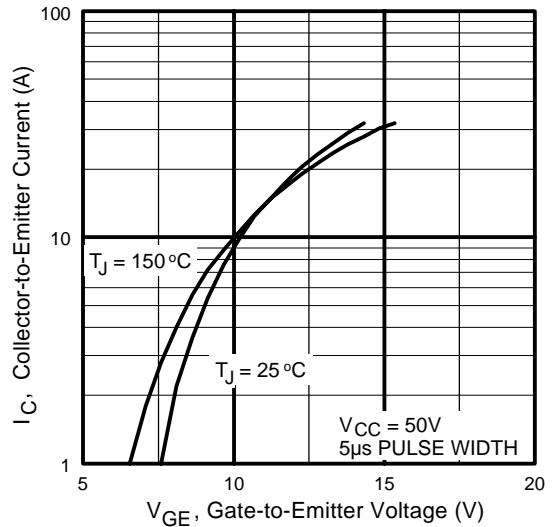


Fig. 3 - Typical Transfer Characteristics

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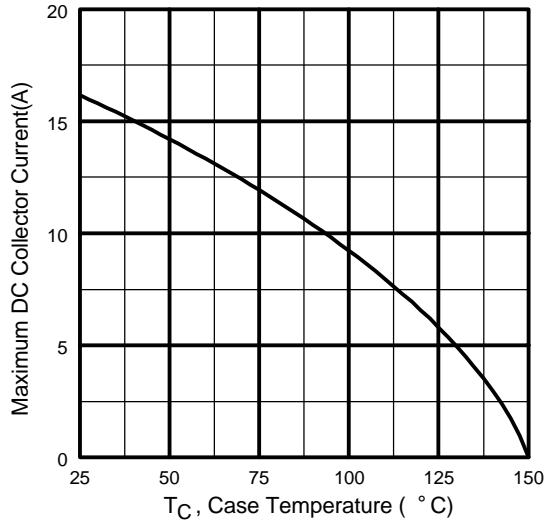


Fig. 4 - Maximum Collector Current vs. Case Temperature

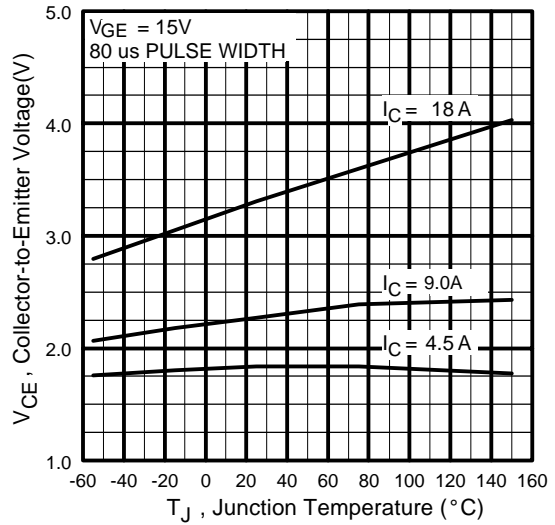


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

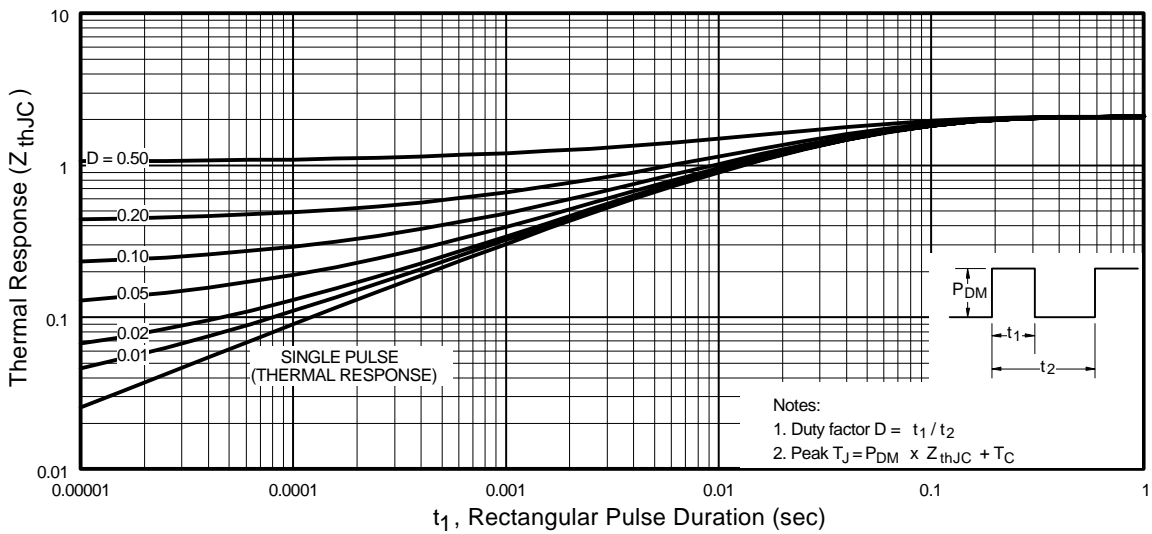


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

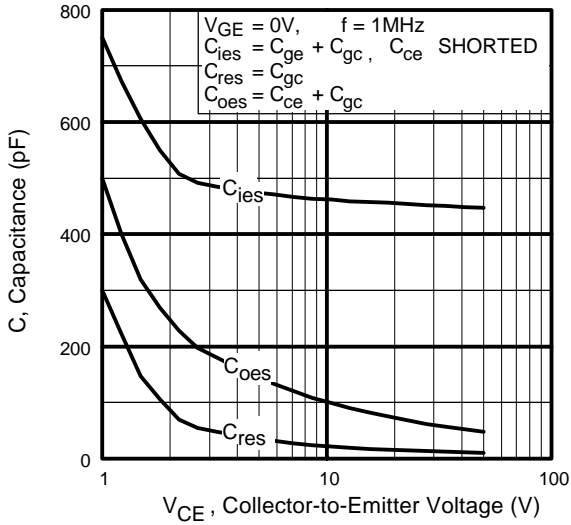


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

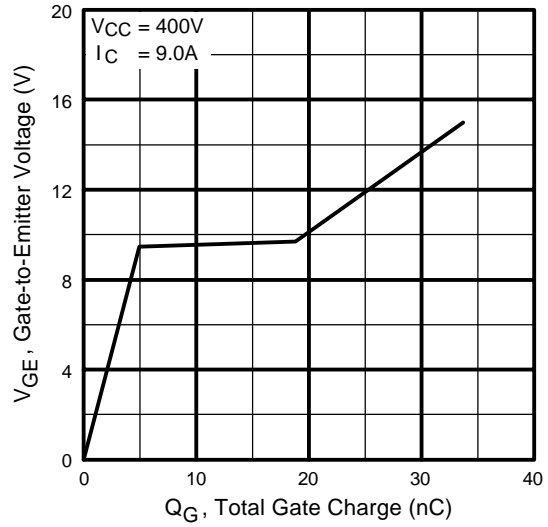


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

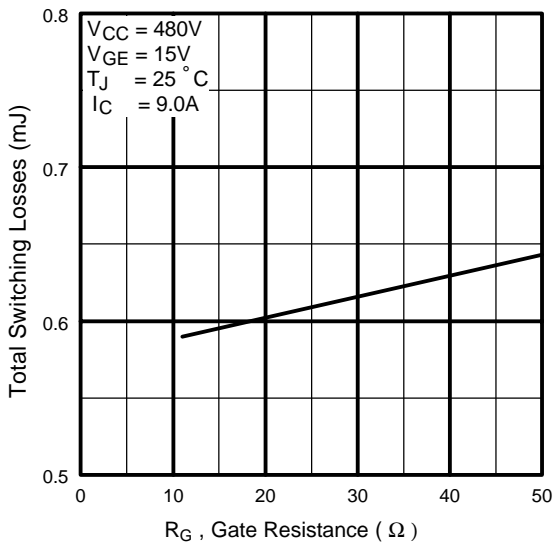


Fig. 9 - Typical Switching Losses vs. Gate Resistance

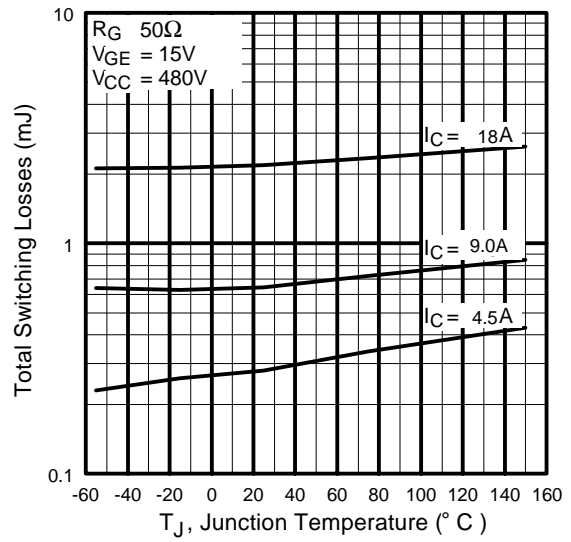


Fig. 10 - Typical Switching Losses vs. Junction Temperature

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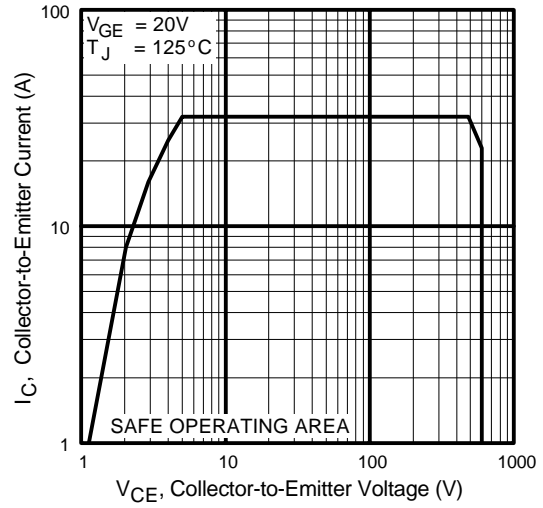
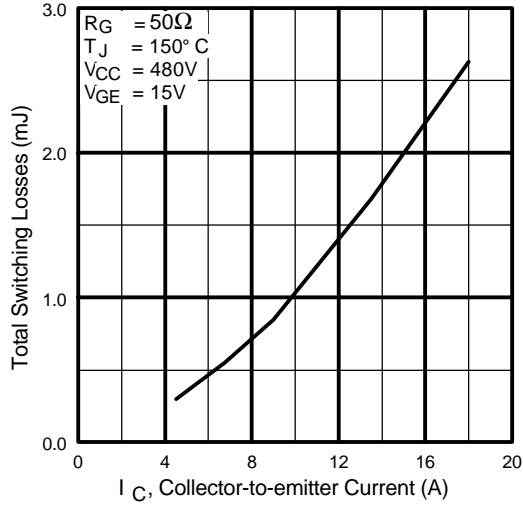


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

Fig. 12 - Turn-Off SOA

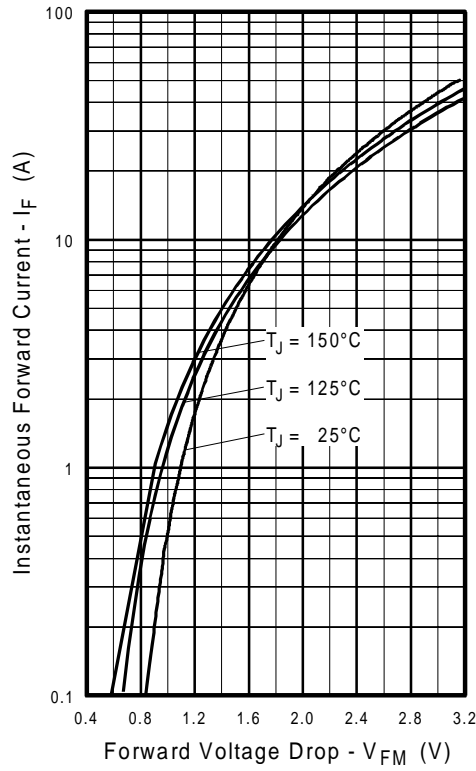


Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

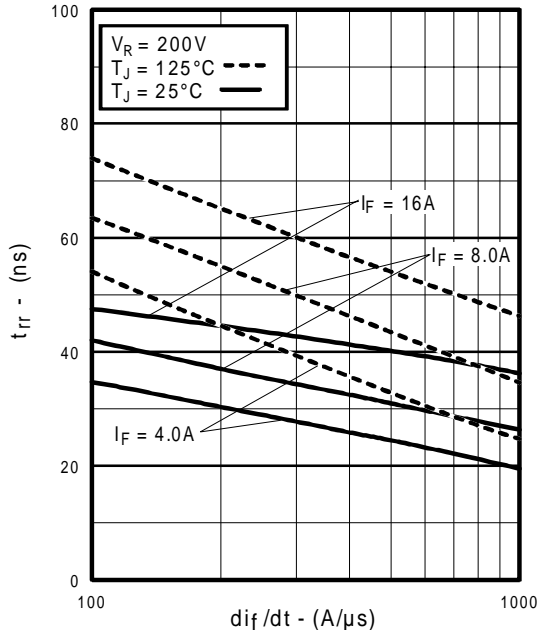


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

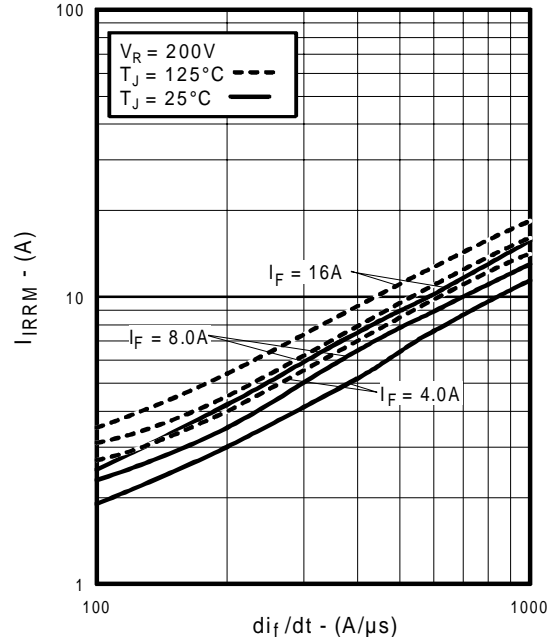


Fig. 15 - Typical Recovery Current vs. di_f/dt

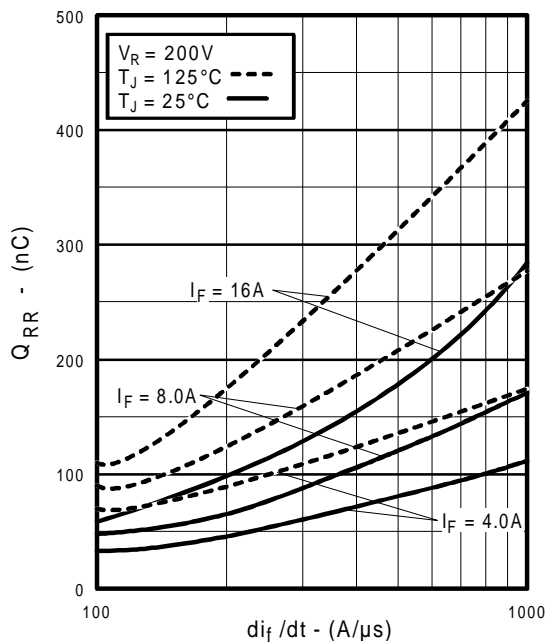


Fig. 16 - Typical Stored Charge vs. di_f/dt

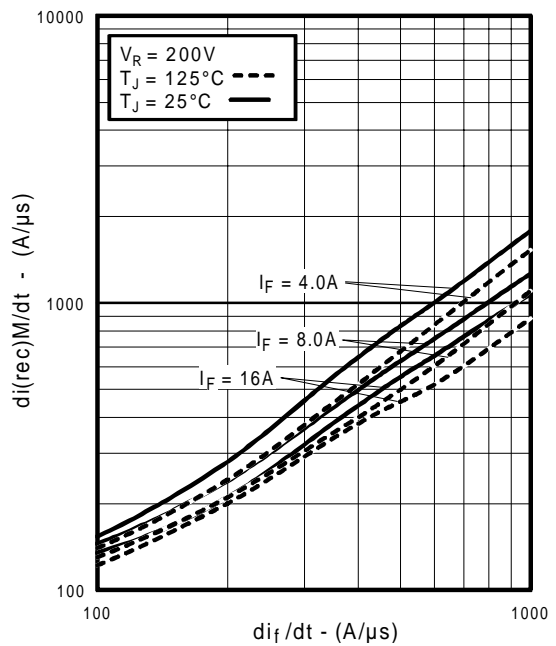


Fig. 17 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

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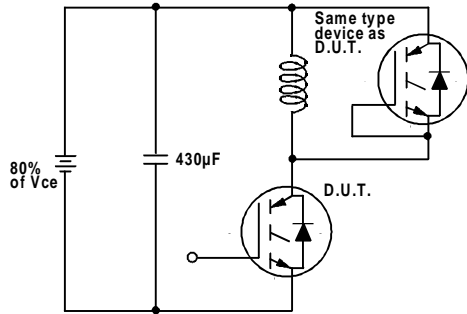


Fig. 18a - Test Circuit for Measurement of I_{LM} , E_{on} , $E_{off}(\text{diode})$, t_{rr} , Q_{rr} , I_{rr} , $t_{d(on)}$, t_r , $t_{d(off)}$, t_f

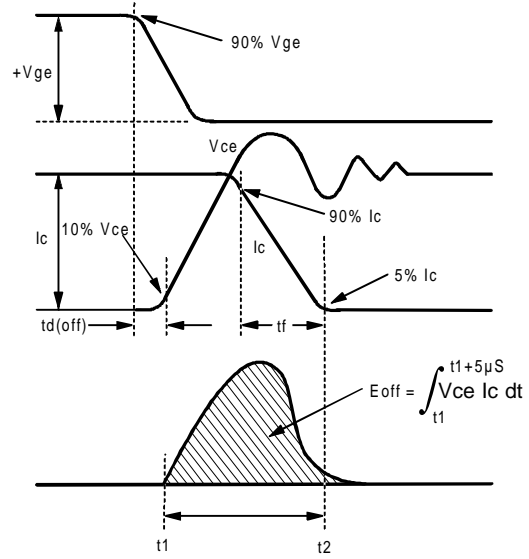


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off} , $t_{d(off)}$, t_f

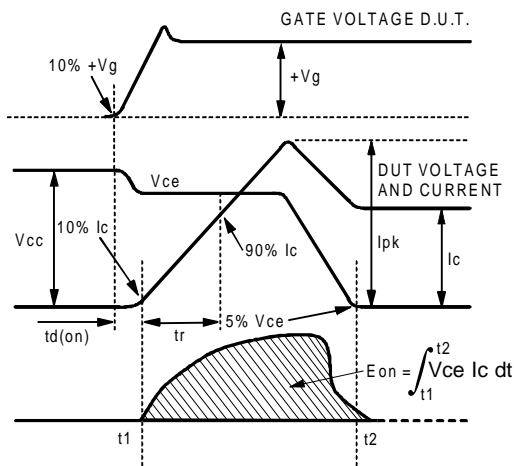


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on} , $t_{d(on)}$, t_r

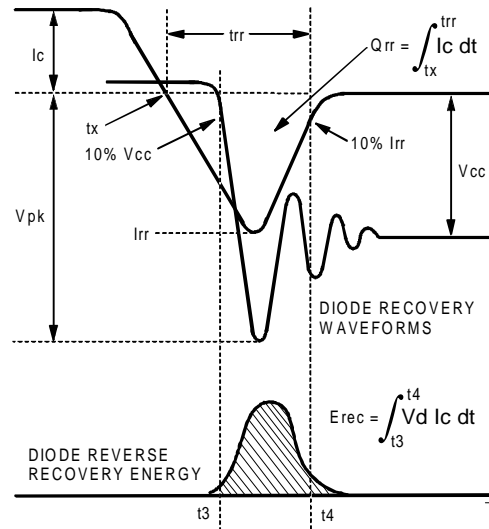


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec} , t_{rr} , Q_{rr} , I_{rr}

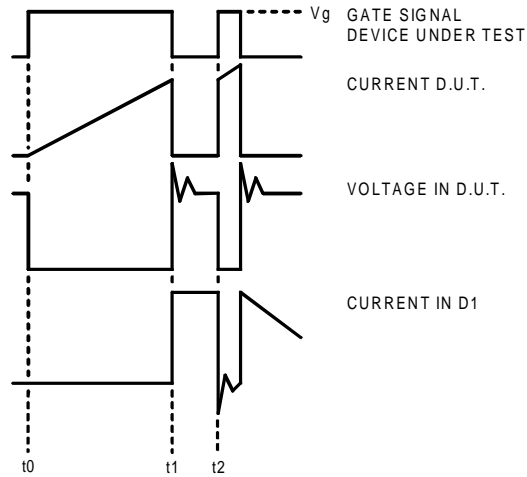


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit



Figure 19. Clamped Inductive Load Test Circuit



Figure 20. Pulsed Collector Current Test Circuit

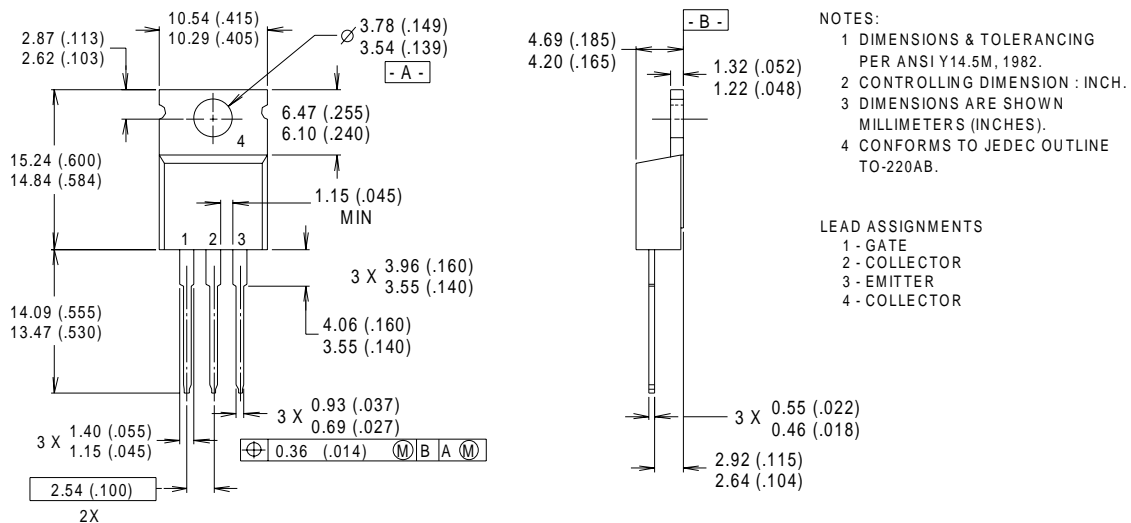
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International
IR Rectifier

Notes:

- ① Repetitive rating: $V_{GE}=20V$; pulse width limited by maximum junction temperature (figure 20)
- ② $V_{CC}=80\%(V_{CES})$, $V_{GE}=20V$, $L=10\mu H$, $R_G=50\Omega$ (figure 19)
- ③ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ④ Pulse width $5.0\mu s$, single shot.

Case Outline — TO-220AB



CONFORMS TO JEDEC OUTLINE TO-220AB

Dimensions in Millimeters and (Inches)

International
IR Rectifier

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IR CANADA: 15 Lincoln Court, Brampton, Ontario L6T3Z2, Tel: (905) 453 2200
IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 (0) 6172 96590
IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 011 451 0111
IR JAPAN: K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo 171 Tel: 81 (0)3 3983 0086
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Data and specifications subject to change without notice. 10/00